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Comparative Analysis of C_comp Extraction Techniques for High-Fidelity IBIS I/O Buffer Modeling

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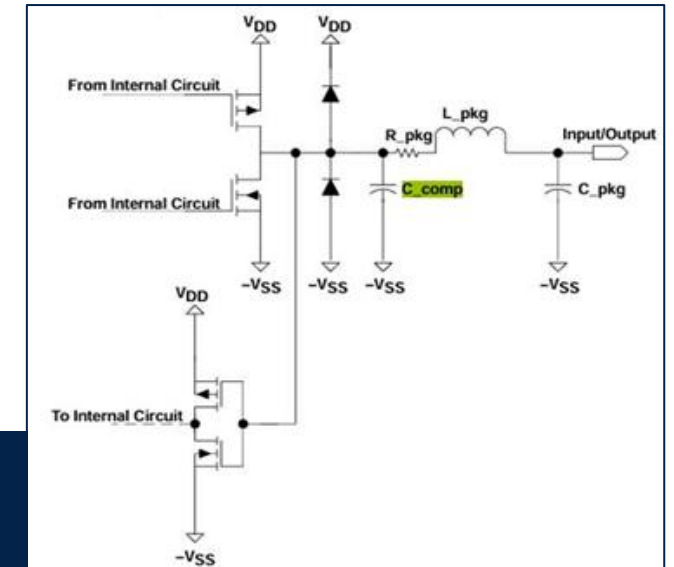


Introduction

- **C_{comp}** is the static equivalent die capacitance of an I/O buffer — capturing pad, on-die interconnect, and intrinsic transistor capacitances — excluding package parasitics.
- Strongly affects:
 - Signal rise/fall times and shape
 - Impedance matching & reflections
 - Timing margins and crosstalk
 - Power integrity and system performance

Accurate C_{comp} extraction improves early prediction of SI issues and enables reliable IBIS models for high-speed designs.

Challenge: C_{comp} is nonlinear and varies with voltage and frequency, making extraction difficult.



Extraction Methods (1/2)

To satisfy the IBIS specification's requirement for a static C_comp entry, each technique described herein maps the buffer's nonlinear, bias- and frequency-dependent die capacitance onto a single representative scalar value.

❑ Forced Saw Tooth technique

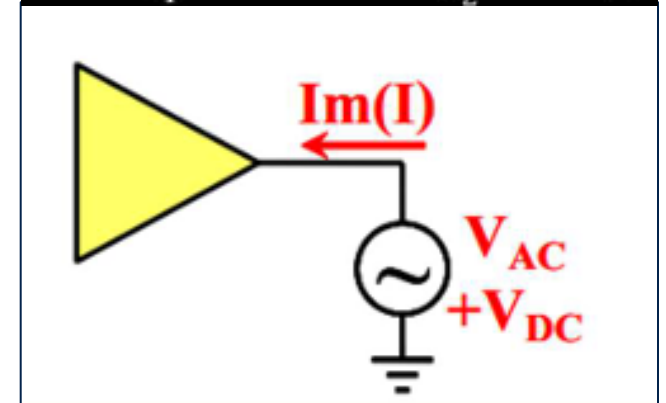
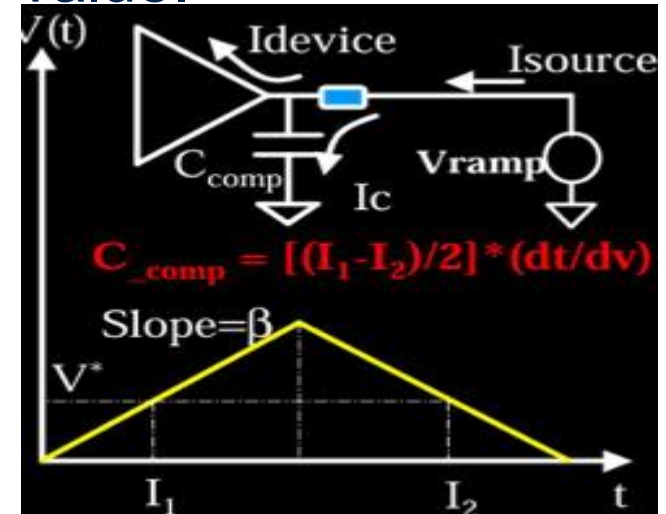
$$C = (I_1 - I_2) / 2\beta$$

- ✓ Isolates capacitive current via differential measurement.
- ⚠ Sensitive to ramp slope; shows voltage but not frequency dependence.

❑ AC / Frequency Sweep analysis

$$C_{\text{comp}} = -\text{Im}(IAC) / (2\pi f \cdot V_{AC})$$

- ✓ Linearizes nonlinear circuits; black-box approach; stable scalar value.
- ⚠ Frequency ambiguity in direct sweep; mitigated by bias-point iteration.



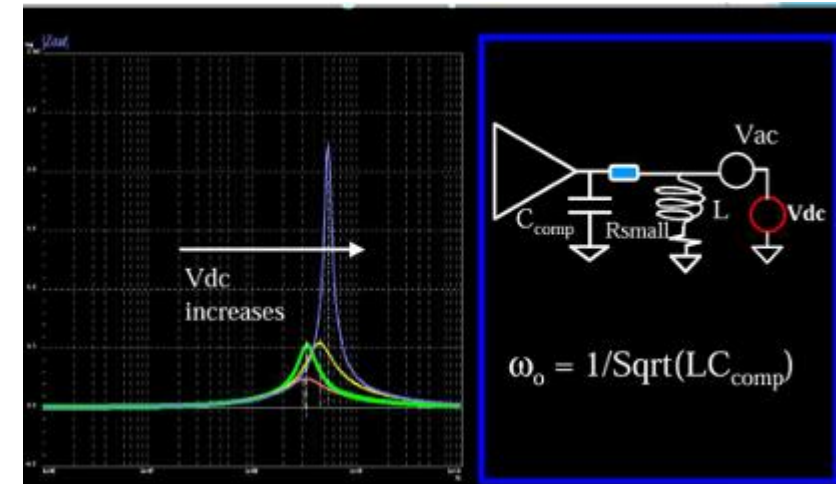
Extraction Methods (2/2)

□ Tank / Resonating circuit

$$C_{\text{comp}} = 1 / (\omega_0^2 \cdot L)$$

✓ Yields a single unambiguous scalar C_{comp} value.

⚠ Requires prior estimate of C_{comp} to select L ; tuning difficulty.

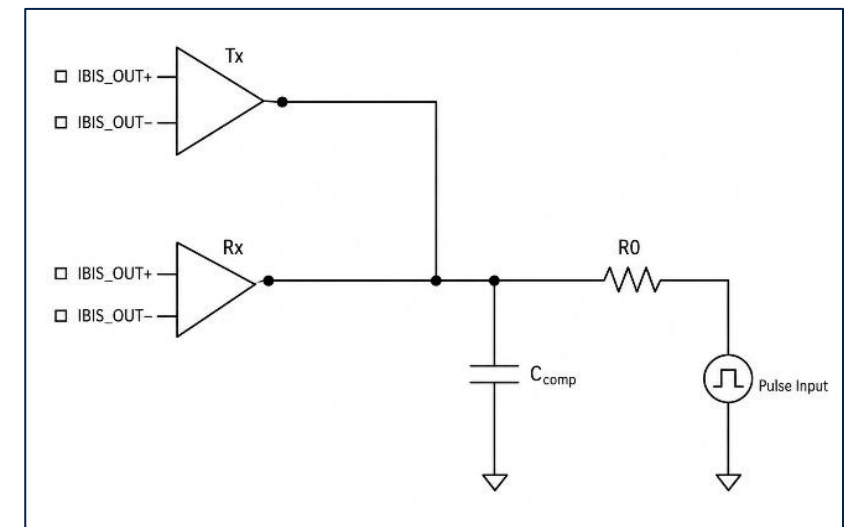


□ RC Time Constant method

$$C_{\text{comp}} = \tau / R = t(V_0=0.632V_s) / R$$

✓ Simple; directly measures time constant.

⚠ Corrupted by DC leakage; approximates dynamic $C(V)$ as static.



- C_comp value comparison

Methodology	C_comp — General-purpose Bidirectional IO	C_comp — Differential IO (LVDS)
Forced Sawtooth	3.2391 pF	1.0912 pF
AC / Frequency Sweep ★	3.2071 pF	1.0800 pF
Tank / Resonating Circuit	3.1904 pF	1.0174 pF
RC Time Constant	3.3604 pF	1.1429 pF

- Observations

- RC Time Constant yields the highest values — inflated by DC leakage current corruption.
- AC/Frequency Sweep produces the most consistent and linearized results across both I/O types.
- C_comp Split delivers lowest values — most structurally accurate.
- All methods converge within ~7% for BIDIR; divergence wider for complex LVDS structures.

Conclusion & Summary

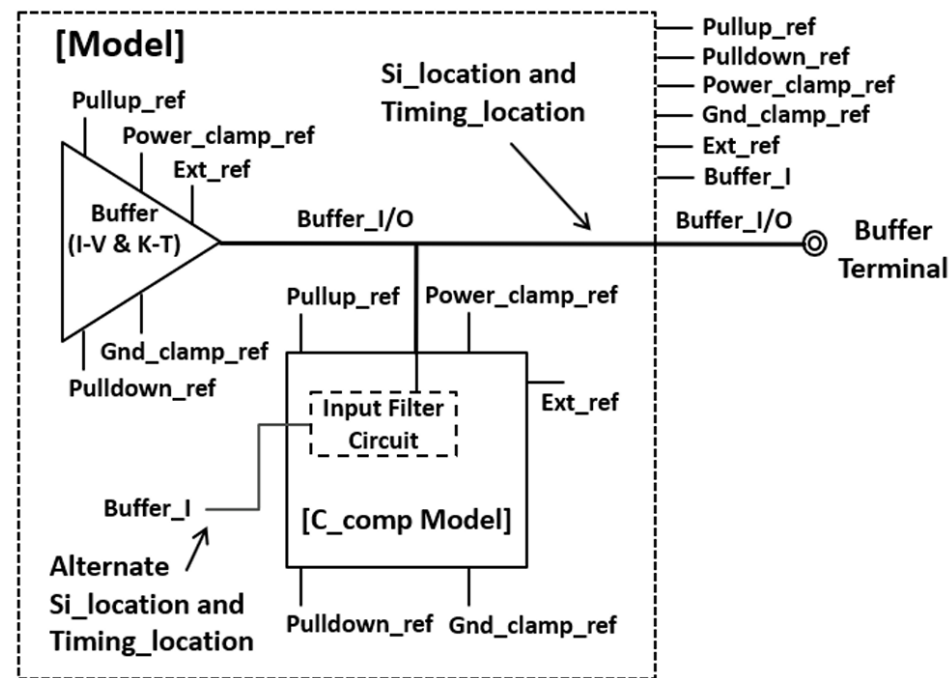
- C_{comp} extraction is essential for high-fidelity IBIS modeling.
- Time-domain and RC-based methods are faster but less robust.
- Tank method gives one value, but tuning is difficult.
- **Recommended approach: AC analysis / frequency sweep**
 - treats buffer as a black box
 - linearizes around a DC bias point
 - provides consistent scalar values
 - best suited for modern SI/PI analysis

For high-speed designs (typically above 1GHz signaling rates or where rise/fall times <500ps),
AC analysis is the preferred standard for reliable IBIS modeling.



Future Work

- Extending the comparative analysis to advanced process nodes.
- Analyze the Impact of C_comp on SI/PI simulations.
- To Explore the [C Comp Model] keyword (BIRD200) keyword in IBIS 7.1,
 - allows for advanced, frequency-dependent, and voltage-dependent capacitance modeling of I/O buffers using IBIS-ISS subcircuits or Touchstone files.



[C_comp Model structure]

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